EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L17	13	(US-20050023596-$ or US-20040119064-$ or US-20050009276-$).did. or (US-6153494-$ or US-5851881-$ or US-6461915-$ or US-6271143-$ or US-5943585-$ or US-5278438-$ or US-6882025-$ or US-5854114-$ or US-6753569-$ or US-5387534-$).did.	US-PGPUB; USPAT	OR	ON	2006/03/21 11:32
L18	10879	semiconductor and (substrate or wafer or board) and conduct$4 and (insulat$4 or dielectric) and (trench or opening or slot or groove) and gate and (spacer or sidewall or (side adj wall)) and planariz$4 and (pattern$3 or remov$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:40
L19	9960	18 and ((liner or insulat$3 or dielectric or $2oxid$4) with (trench or opening or slot or groove or via))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:41
L20	4415	19 and (self-align$3 or (self near2 align$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:43
L21	4211	20 and (gate with (dielectric or insulat$3 or $2oxid$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:48
L22	3599	21 and ((spacer or sidewall or (side adj wall)) with (remov$4 or etch$3 or pattern$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:50
L23	3242	22 and (@ad<"20030731" or @rlad<"20030731")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 14:00
L24	3154	23 and (mask$4 or resist$3 or maskresist$3 or photomask or photoresist)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:42
L25	235	24 and (semiconductor and (substrate or wafer or board) and conduct$4 and (insulat$4 or dielectric) and (trench or opening or slot or groove) and gate and (spacer or sidewall or (side adj wall)) and planariz$4 and (pattern$3 or remov$3)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:48
L26	216	25 and ((liner or insulat$3 or dielectric or $2oxid$4) with (trench or opening or slot or groove or via)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:44
L27	173	26 and (((spacer or sidewall or (side adj wall)) with (remov$4 or etch$3 or pattern$3)) and ((spacer or sidewall or (side adj wall)) with (remov$4 or etch$3 or pattern$3))).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:42
L28	93	27 and (self-align$3 or (self near2 align$3)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:52
L29	86	28 and (fill$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:44

EAST Search History

L30	84	28 and ((liner or insulat$3 or dielectric or $2oxid$4) with (trench or opening or slot or groove or via) with fill$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:51
L31	213	(semiconductor and (substrate or wafer or board) and conduct$4 and (insulat$4 or dielectric or $2oxid$4) and (trench or via or opening or slot or groove) and gate and (spacer or sidewall or (side adj wall)) and planariz$4 and (pattern$3 or remov$3) and (gate with (dielectric or insulat$3 or $2oxid$4))). clm.	US-PGPUB	OR	ON	2006/03/21 14:11
L32	162	31 and (((spacer or sidewall or (side adj wall)) with (remov$4 or etch$3 or pattern$3))).clm.	US-PGPUB	OR	ON	2006/03/21 11:50
L33	90	32 and ((liner or insulat$3 or dielectric or $2oxid$4) with (trench or opening or slot or groove or via) with fill$3).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:51
L34	37	33 and (self-align$3 or (self near2 align$3)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 11:52
L35	2521	438/261,400,700.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 13:03
L36	43	35 and (semiconductor and (substrate or wafer or board) and conduct$4 and (insulat$4 or dielectric or $2oxid$4) and (trench or via or opening or slot or groove) and gate and (spacer or sidewall or (side adj wall)) and planariz$4 and (pattern$3 or remov$3) and (gate with (dielectric or insulat$3 or $2oxid$4)))	US-PGPUB	OR	ON	2006/03/21 14:07
L37	42	36 not (17 34)	US-PGPUB	OR	ON	2006/03/21 13:55
L38	34	37 and (@ad<"20030731" or @rlad<"20030731")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 14:07
L39	98	438/400.ixr.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 14:11
L40	3	39 and (semiconductor and (substrate or wafer or board) and conduct$4 and (insulat$4 or dielectric or $2oxid$4) and (trench or via or opening or slot or groove) and gate and (spacer or sidewall or (side adj wall)) and planariz$4 and (pattern$3 or remov$3) and (gate with (dielectric or insulat$3 or $2oxid$4)))	US-PGPUB	OR	ON	2006/03/21 14:10
L41	3	39 and (semiconductor and (substrate or wafer or board) and conduct$4 and (insulat$4 or dielectric or $2oxid$4) and (trench or via or opening or slot or groove) and gate and (spacer or sidewall or (side adj wall)) and planariz$4)	US-PGPUB	OR	ON	2006/03/21 14:10
L42	711	438/400.cxr.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 14:14
L43	3	42 and (semiconductor and (substrate or wafer or board) and conduct$4 and (insulat$4 or dielectric or $2oxid$4) and (trench or via or opening or slot or groove) and gate and (spacer or sidewall or (side adj wall)) and planariz$4 and (pattern$3 or remov$3))	US-PGPUB	OR	ON	2006/03/21 14:12
L44	9	42 and (semiconductor and (substrate or wafer or board) and conduct$4 and (insulat$4 or dielectric or $2oxid$4) and (trench or via or opening or slot or groove) and gate and (spacer or sidewall or (side adj wall)))	US-PGPUB	OR	ON	2006/03/21 14:12

EAST Search History

L45	876	438/400.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 14:35
L46	0	H01L21/311.FIPC.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 14:31
L47	0	21/311.FIPC.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 14:23
L48	0	21/311.FIPC.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/21 14:23
L50	24	H01L21/311.IPC.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 14:32
L51	1094	438/700.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 14:36
L52	1990	257/E21.582.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 15:33
L53	570	257/E21.295.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/03/21 15:33
S1	1	"20050023596"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/28 19:44
S2	139	Hsieh-Chia-ta.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/28 19:44
S3	1	S1 and (trench or strip$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/28 19:44
S4	101	S2 and (trench or strip$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/28 19:44
S5	10	S4 and liner	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/28 19:45

EAST Search History

S6	1	"20050023596"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/29 10:26
S7	139	Hsieh-Chia-ta.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/29 10:26
S8	1	S6 and (trench or strip$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/29 10:26
S9	101	S7 and (trench or strip$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/29 10:26
S10	10	S9 and liner	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/04/29 10:26
S11	9	("5231299" | "5447884" | "5597751" | "5652161" | "5851881" | "6017795" | "6074927" | "6093611" | "6110800").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/29 10:47
S12	7	("5173436" | "5293560" | "5387534" | "5480821" | "5496753" | "5515321" | "5559048").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/29 10:56
S13	33	("5851881").URPN.	USPAT	OR	ON	2005/04/29 11:44
S14	14	("5427968" | "5614747" | "5652161" | "5851881" | "5858840" | "5879992" | "5918125" | "5950087" | "5981340" | "5989960" | "6005807" | "6130132" | "6133098" | "6153494").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/29 11:51
S15	13	("6204126").URPN.	USPAT	OR	ON	2005/04/29 12:00
S16	6	("6358796").URPN.	USPAT	OR	ON	2005/04/29 12:05
S17	13	("6204126").URPN.	USPAT	OR	ON	2005/04/29 12:09
S18	1	"6753569"	USPAT	OR	ON	2005/04/29 12:10
S19	7	("4631803" | "5231299" | "5447884" | "5597751" | "5652161" | "5851881" | "6013551").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/29 12:13
S20	7	("4631803" | "5231299" | "5447884" | "5597751" | "5652161" | "5851881" | "6013551").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/04/29 12:13
S21	0	("6753569").URPN.	USPAT	OR	ON	2005/04/29 12:14
S22	8	(US-20020055205-$ or US-20050023596-$).did. or (US-5387534-$ or US-5851881-$ or US-6153494-$ or US-6204126-$ or US-6734055-$ or US-6753569-$).did.	US-PGPUB; USPAT	OR	ON	2005/08/16 16:29
S23	4	("4914050" | "4975384" | "5234856" | "5278438").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/16 16:43
S24	7	("5173436" | "5293560" | "5387534" | "5480821" | "5496753" | "5515321" | "5559048").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/21 13:21
S25	37	("5851881").URPN.	USPAT	OR	ON	2005/10/21 13:23
S26	180	transistor and ((trench adj isolat$3) with (oxide near3 liner))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 13:29

EAST Search History

S27	147	transistor and ((trench adj isolat$3) with (oxide near liner))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 13:30
S28	98	S27 and gate and (spacer or sidewall or (side adj wall))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 13:31
S29	42	S28 and (remov$3 with (spacer or sidewall or (side adj wall)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 13:31
S30	39	S29 and ((chemical adj vapor$3 adj2 process$3) or "CMP")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 13:32
S31	32	S30 and well	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 13:32
S32	13	S31 and float$4 and polysilicon	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 13:42
S33	19	S31 not S32	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 13:57
S34	6	("4797718" | "4912535" | "5043787" | "5053839" | "5084418" | "5218221").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/21 13:53
S35	43	("5278438").URPN.	USPAT	OR	ON	2005/10/21 13:54
S36	10	S29 not S31	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 13:58
S37	56	S28 not S29	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 13:58
S38	1	10/723842 and gibb	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/10/21 14:59